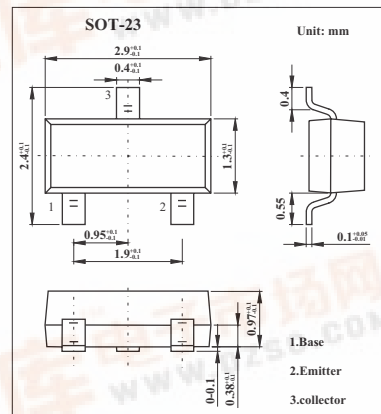


SMD Type Transistors

Silicon PNP Epitaxia  
2SA1362

Features

- Suitable for driver stage of small motor.
- Small package.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-15	V
Collector-emitter voltage	V <sub>CE0</sub>	-15	V
Emitter-base voltage	V <sub>EB0</sub>	-5	V
Collector current	I <sub>C</sub>	-800	mA
Base current	I <sub>B</sub>	-160	mA
Collector dissipation	P <sub>C</sub>	200	mW
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -15 V, I <sub>E</sub> = 0			-100	nA
Emitter cut-off current	I <sub>EB0</sub>	V <sub>EB</sub> = -5 V, I <sub>C</sub> = 0			-100	nA
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -10 mA, I <sub>B</sub> = 0	-15			V
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = -1 V, I <sub>C</sub> = -100 mA	120		400	
Collector-emitter saturation voltage	V <sub>J</sub>	I <sub>C</sub> = -400 mA, I <sub>B</sub> = -8 mA			-0.2	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = -1 V, I <sub>C</sub> = -10 mA	-0.5		-0.8	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -5 V, I <sub>C</sub> = -10 mA		120		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz		13		pF

hFE Classification

Marking	AE	
	Y	G
h <sub>FE</sub>	120-240	200~400

